

7MBR50VP060-50

IGBT Modules

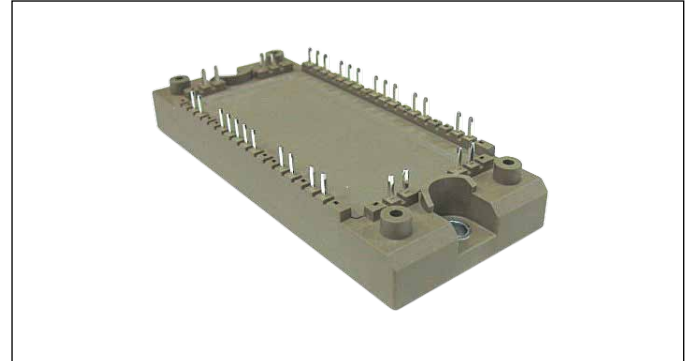
IGBT MODULE (V series) 600V / 50A / PIM

■ Features

- Low $V_{CE(sat)}$
- Compact Package
- P.C.Board Mount Module
- Converter Diode Bridge Dynamic Brake Circuit
- RoHS compliant product

■ Applications

- Inverter for Motor Drive
- AC and DC Servo Drive Amplifier
- Uninterruptible Power Supply



■ Maximum Ratings and Characteristics

● Absolute Maximum Ratings (at $T_c=25^\circ\text{C}$ unless otherwise specified)

Items		Symbols	Conditions	Maximum ratings	Units	
Inverter	Collector-Emitter voltage	V_{CES}		600	V	
	Gate-Emitter voltage	V_{GES}		± 20	V	
	Collector current	I_c	Continuous	$T_c=80^\circ\text{C}$	50	A
		I_{cp}	1ms	$T_c=80^\circ\text{C}$	100	
		$-I_c$			50	
$-I_c$ pulse		1ms		100		
Collector power dissipation	P_c	1 device		200	W	
Brake	Collector-Emitter voltage	V_{CES}		600	V	
	Gate-Emitter voltage	V_{GES}		± 20	V	
	Collector current	I_c	Continuous	$T_c=80^\circ\text{C}$	50	A
		I_{cp}	1ms	$T_c=80^\circ\text{C}$	100	
	Collector power dissipation	P_c	1 device		200	W
Repetitive peak reverse voltage (Diode)	V_{RRM}			600	V	
Converter	Repetitive peak reverse voltage	V_{RRM}		800	V	
	Average output current	I_o	50Hz/60Hz, sine wave	50	A	
	Surge current (Non-Repetitive)	I_{FSM}	10ms, $T_j=150^\circ\text{C}$	210	A	
	I^2t (Non-Repetitive)	I^2t	half sine wave	221	A^2s	
Junction temperature	T_j	Inverter, Brake		175	$^\circ\text{C}$	
		Converter		150		
Operating junction temperature (under switching conditions)	T_{jop}	Inverter, Brake		150		
		Converter		150		
Case temperature	T_c			125		
Storage temperature	T_{stg}			-40 to +125		
Isolation voltage	between terminal and copper base (*1) between thermistor and others (*2)	V_{iso}	AC : 1min.	2500	VAC	
Screw torque	Mounting (*3)	-	M5	3.5	N m	

Note *1: All terminals should be connected together during the test.

Note *2: Two thermistor terminals should be connected together, other terminals should be connected together and shorted to base plate during the test.

Note *3: Recommendable value : 2.5-3.5 Nm (M5)

● Electrical characteristics (at T_j = 25°C unless otherwise specified)

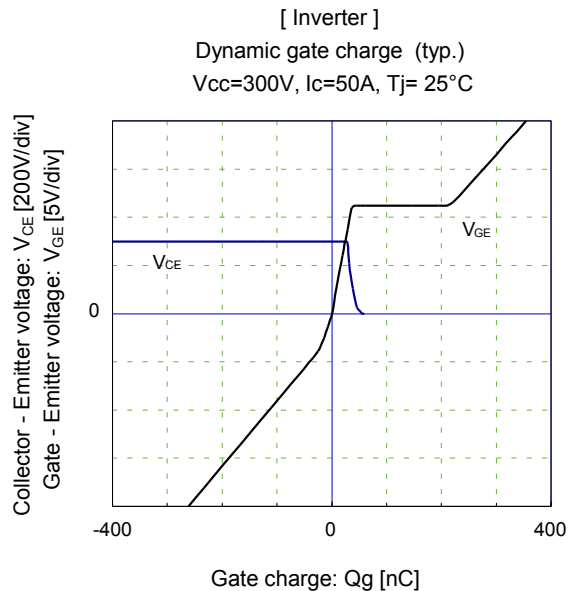
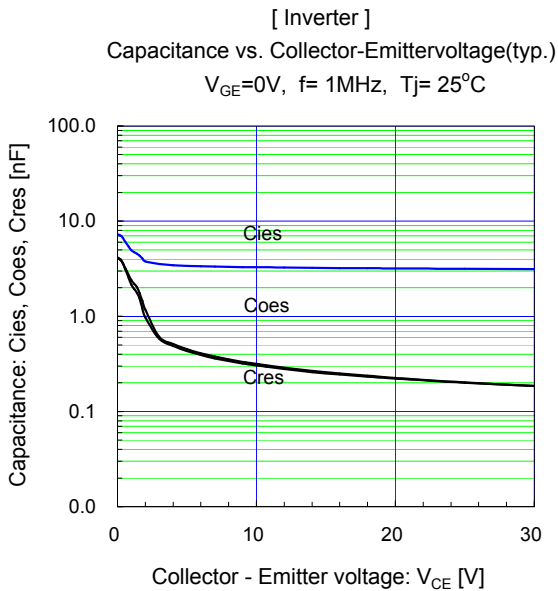
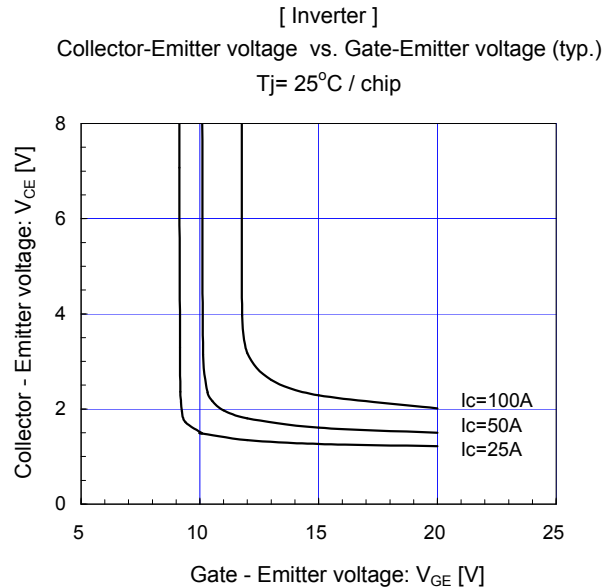
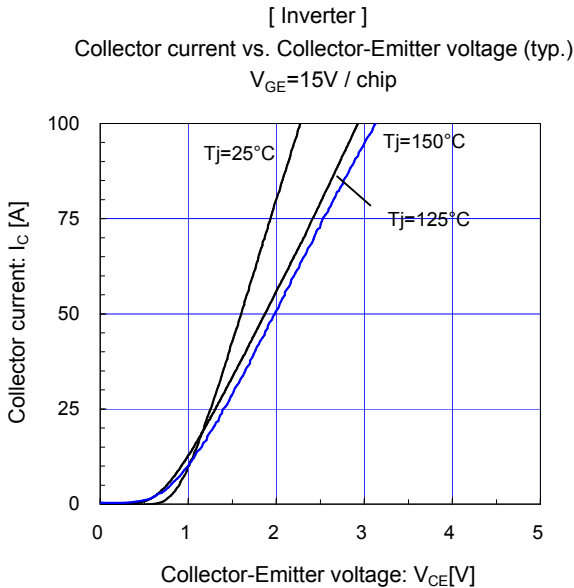
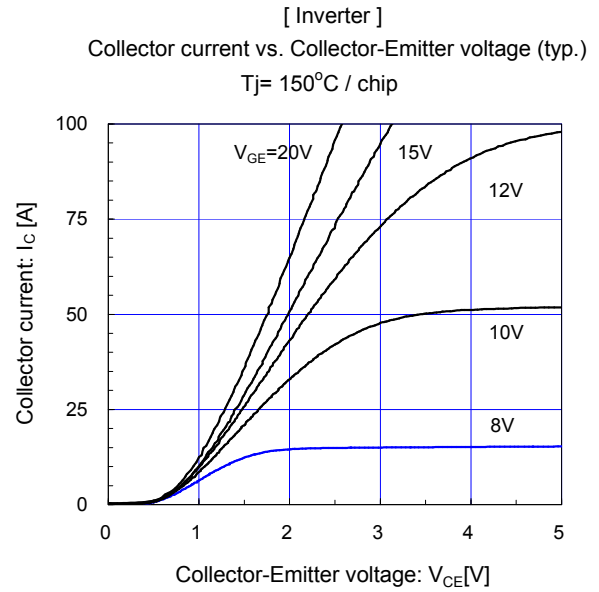
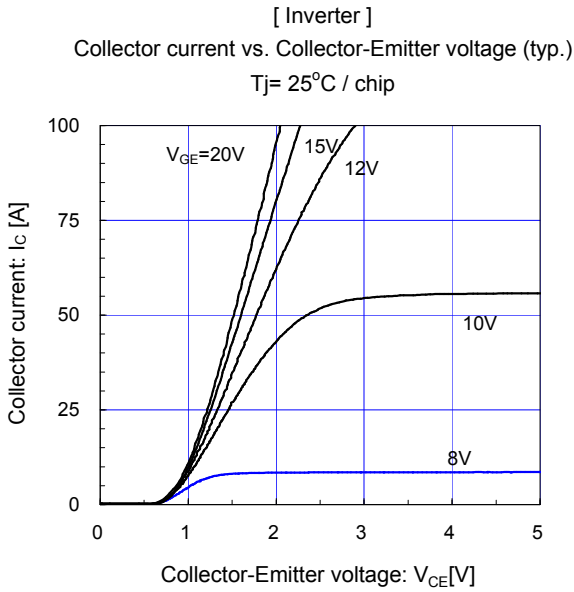
Items	Symbols	Conditions	Characteristics			Units		
			min.	typ.	max.			
Inverter	Zero gate voltage collector current	I _{CES}	V _{GE} = 0V, V _{CE} = 600V	-	-	1.0	mA	
	Gate-Emitter leakage current	I _{GES}	V _{GE} = 0V, V _{CE} = ±20V	-	-	200	nA	
	Gate-Emitter threshold voltage	V _{GE(th)}	V _{CE} = 20V, I _c = 50mA	6.2	6.7	7.2	V	
	Collector-Emitter saturation voltage	V _{CE(sat)} (terminal)	V _{GE} = 15V I _c = 50A	T _j = 25°C	-	1.85	2.30	V
				T _j = 125°C	-	2.15	-	
				T _j = 150°C	-	2.25	-	
		V _{CE(sat)} (chip)	V _{GE} = 15V I _c = 50A	T _j = 25°C	-	1.60	2.05	
				T _j = 125°C	-	1.90	-	
	T _j = 150°C	-	2.00	-				
	Internal gate resistance	R _{g(int)}	-	-	0	-	Ω	
	Input capacitance	C _{ies}	V _{CE} = 10V, V _{GE} = 0V, f = 1MHz	-	3.3	-	nF	
	Turn-on time	ton	V _{CC} = 300V I _c = 50A	-	0.36	1.20	μs	
		tr		-	0.25	0.60		
		tr(i)		-	0.07	-		
	Turn-off time	toff	V _{GE} = +15 / -15V R _G = 43Ω	-	0.52	1.20	μs	
tf		-		0.03	0.45			
Forward on voltage	V _F (terminal)	I _F = 50A	T _j = 25°C	-	1.85	2.30	V	
			T _j = 125°C	-	1.75	-		
			T _j = 150°C	-	1.70	-		
	V _F (chip)	I _F = 50A	T _j = 25°C	-	1.60	2.05		
			T _j = 125°C	-	1.50	-		
T _j = 150°C	-	1.45	-					
Reverse recovery time	trr	I _F = 50A	-	-	0.35	μs		
Brake	Zero gate voltage collector current	I _{CES}	V _{GE} = 0V V _{CE} = 600V	-	-	1.0	mA	
	Gate-Emitter leakage current	I _{GES}	V _{CE} = 0V V _{GE} = +20 / -20V	-	-	200	nA	
	Collector-Emitter saturation voltage	V _{CE(sat)} (terminal)	V _{GE} = 15V I _c = 50A	T _j = 25°C	-	1.85	2.30	V
				T _j = 125°C	-	2.15	-	
				T _j = 150°C	-	2.25	-	
		V _{CE(sat)} (chip)	V _{GE} = 15V I _c = 50A	T _j = 25°C	-	1.60	2.05	
				T _j = 125°C	-	1.90	-	
	T _j = 150°C	-	2.00	-				
	Internal gate resistance	R _{g(int)}	-	-	0	-	Ω	
	Turn-on time	ton	V _{CE} = 300V I _c = 50A	-	0.36	1.20	μs	
		tr		-	0.25	0.60		
	Turn-off time	toff	V _{GE} = +15 / -15V R _G = 43Ω	-	0.52	1.20	μs	
		tf		-	0.03	0.45		
	Reverse current	IRRM	V _R = 600V	-	-	1.00	mA	
	Converter	Forward on voltage	V _{FM} (chip)	terminal	-	1.55	2.00	V
chip				-	1.30	-		
Reverse current	IRRM	V _R = 800V	-	-	1.0	mA		
Thermistor	Resistance	R	T = 25°C	-	5000	-	Ω	
			T = 100°C	465	495	520		
	B value	B	T = 25 / 50°C	3305	3375	3450	K	

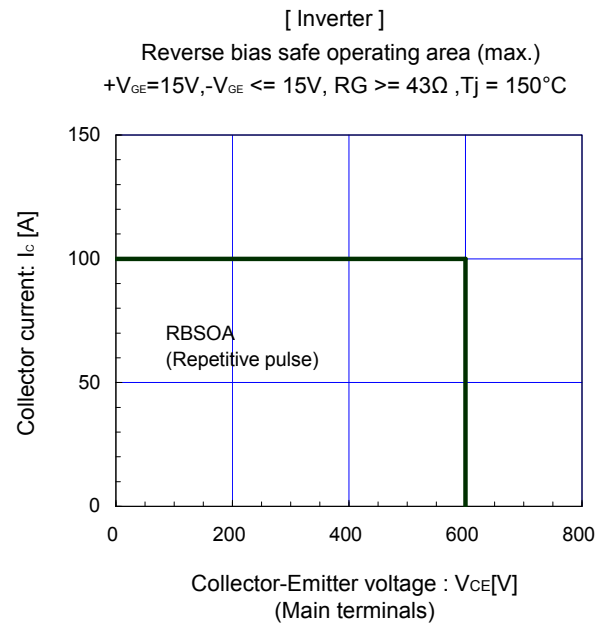
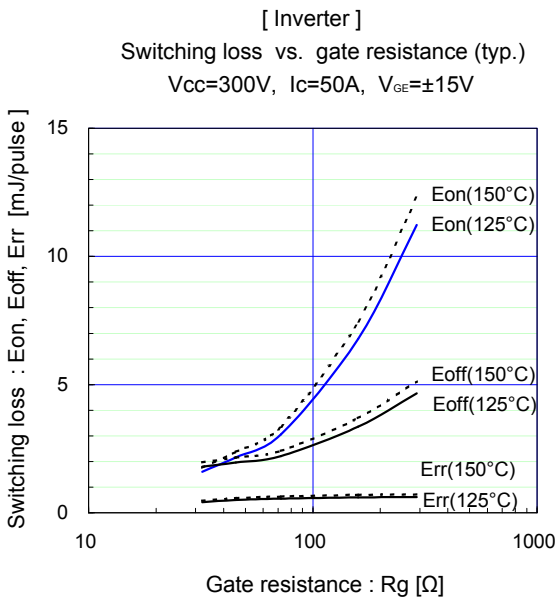
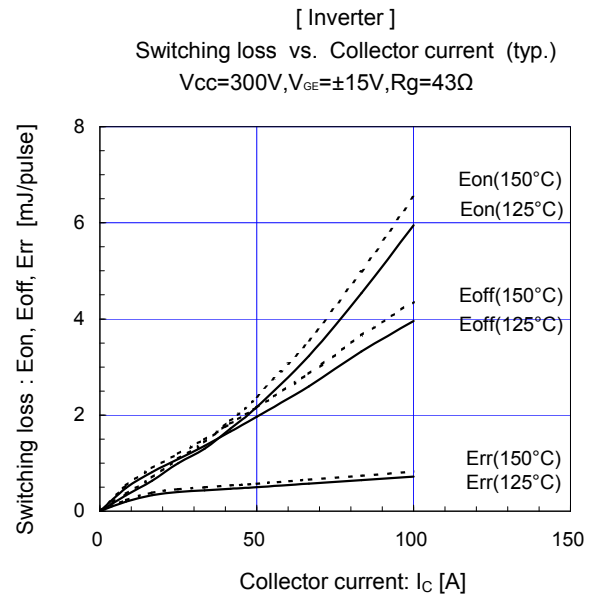
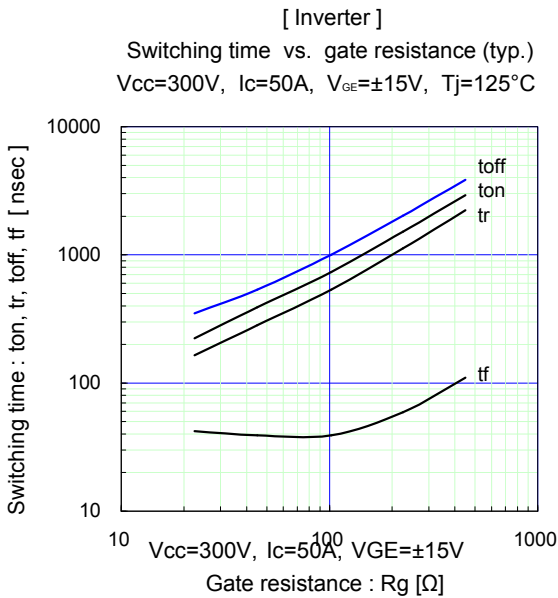
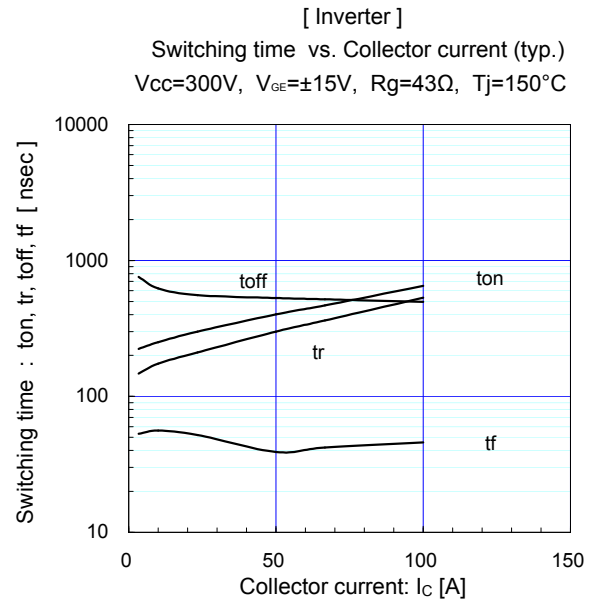
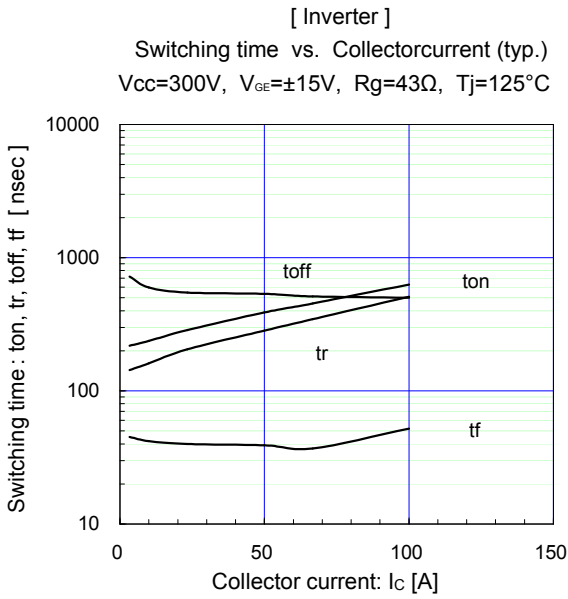
● Thermal resistance characteristics

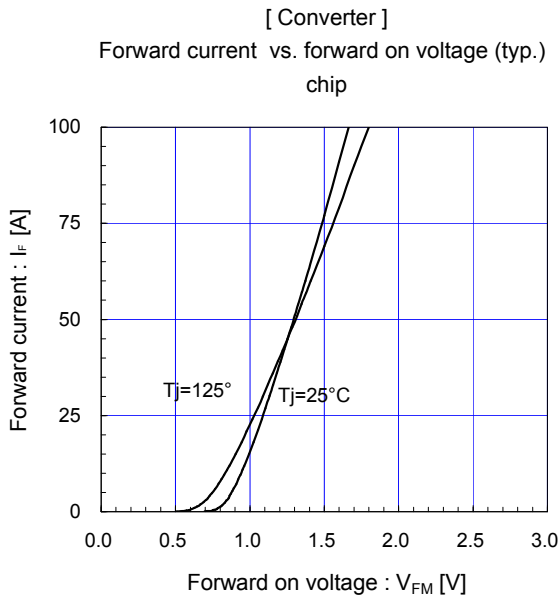
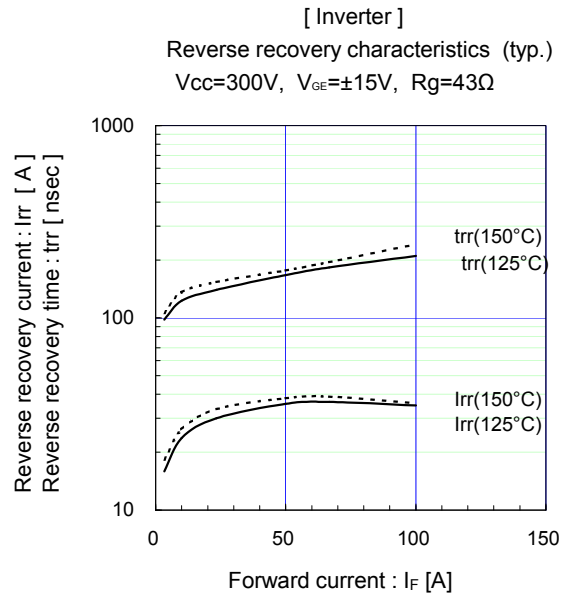
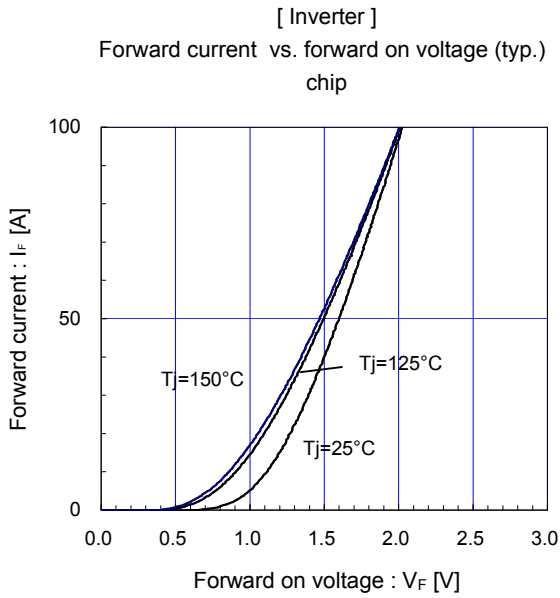
Items	Symbols	Conditions	Characteristics			Units
			min.	typ.	max.	
Thermal resistance (1device)	R _{th(j-c)}	Inverter IGBT	-	-	0.71	°C/W
		Inverter FWD	-	-	1.15	
		Brake IGBT	-	-	0.71	
		Converter Diode	-	-	1.20	
Contact thermal resistance (1device) (*4)	R _{th(c-f)}	with Thermal Compound	-	0.05	-	

Note *4: This is the value which is defined mounting on the additional cooling fin with thermal compound.

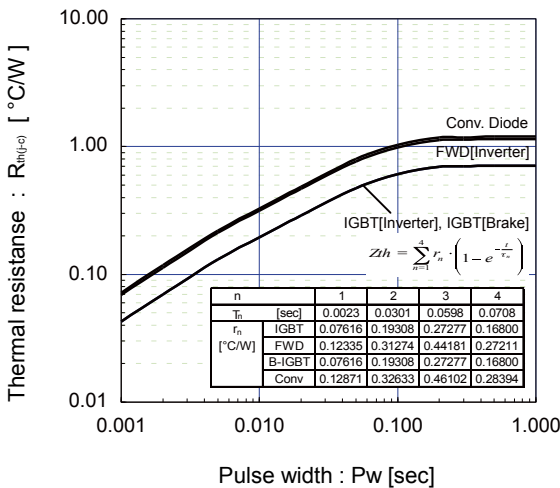
■ Characteristics (Representative)



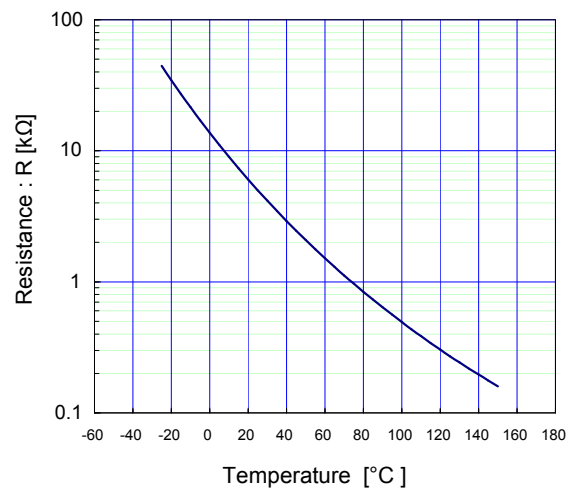


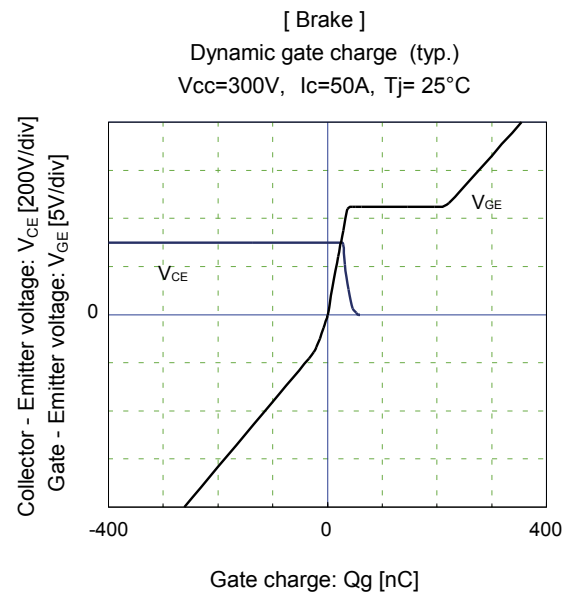
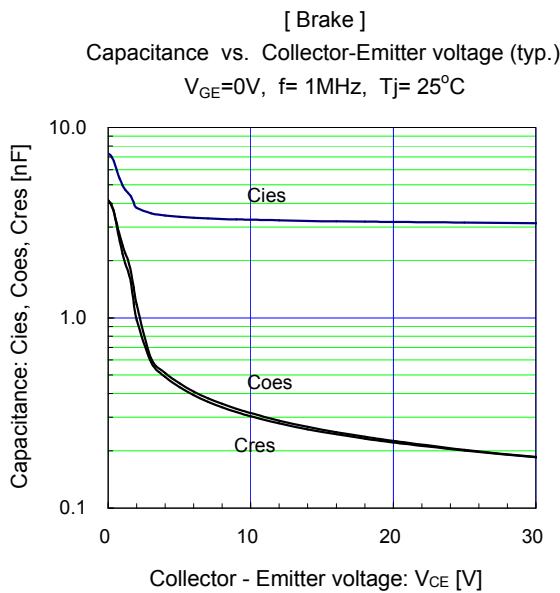
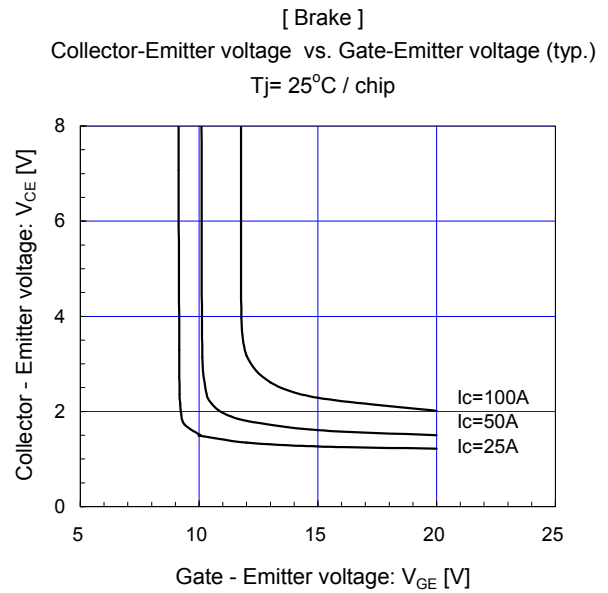
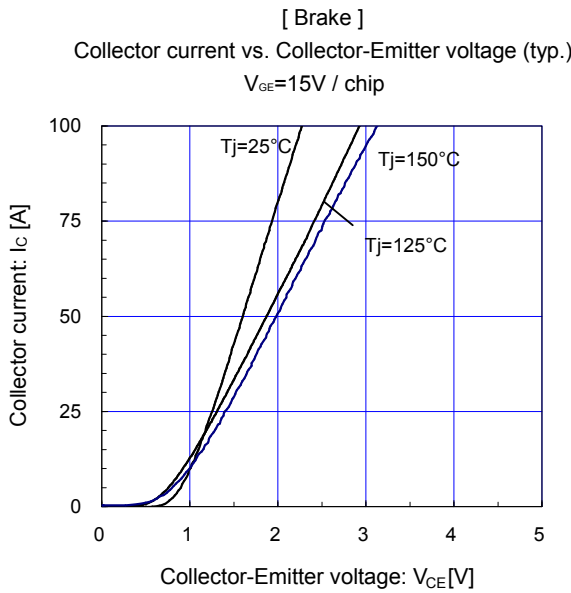
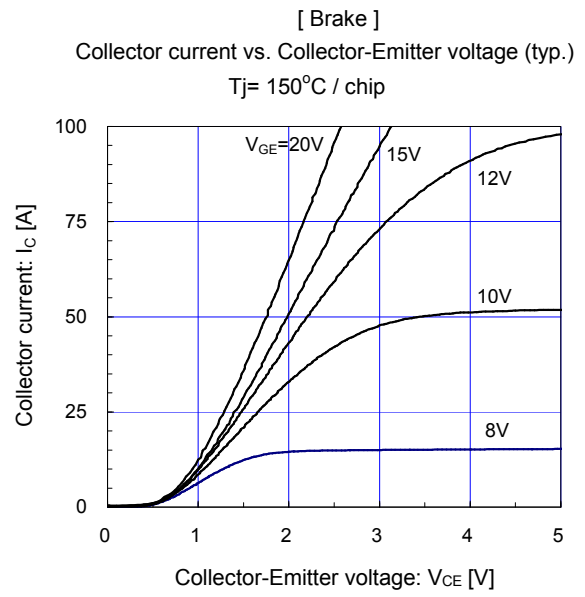
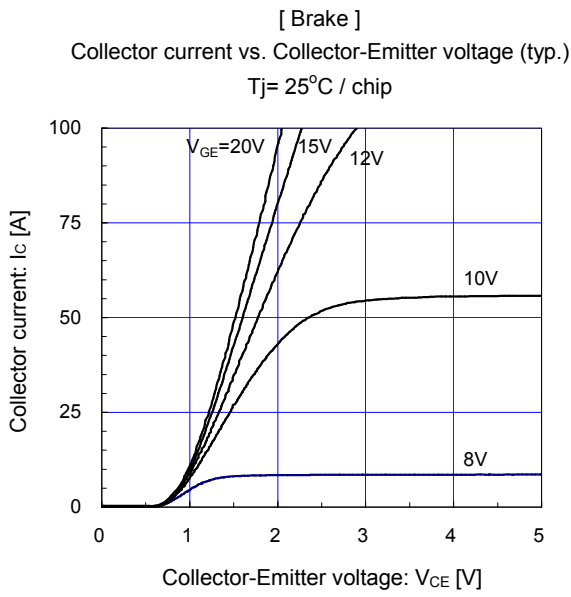


Transient thermal resistance (max.)



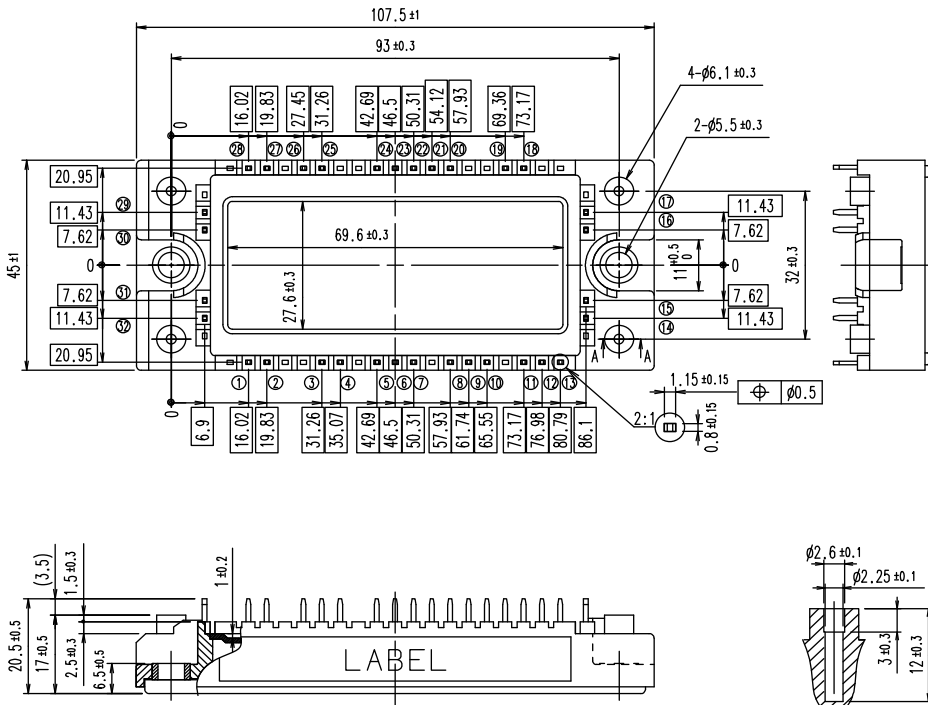
[Thermistor]
Temperature characteristic (typ.)





■ Outline Drawings(Unit:mm)

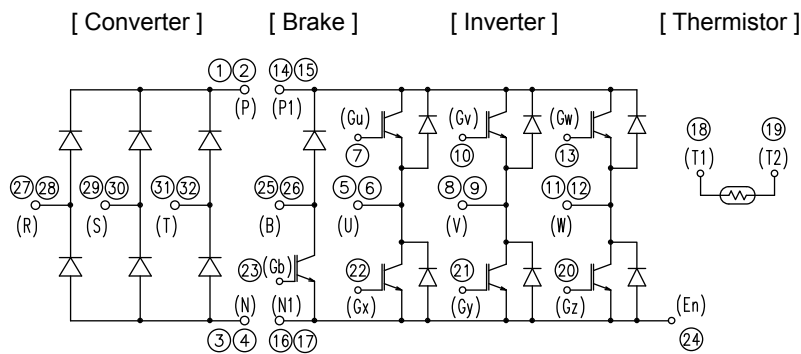
□ shows theoretical dimension.
 () shows reference dimension.



Section A-A

Weight: 200g(typ.)

■ Equivalent Circuit



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IGBT Modules

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